RENESAS BCR8PM-16LG

Triac Medium Power Use

> REJ03G1560-0100 Rev.1.00 Jul 06, 2007

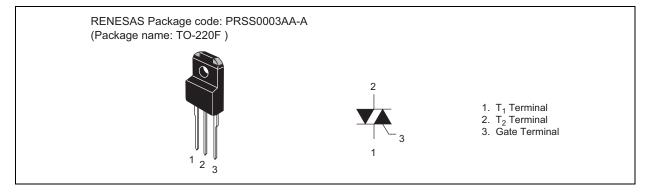
Features

- $I_{T (RMS)}$: 8 A
- V_{DRM} : 800 V
- I_{FGTI} , I_{RGTI} , I_{RGTII} : 30 mA
- Viso : 2000 V

- The Product guaranteed maximum junction temperature 150°C
- Insulated Type
- Planar Type
- UL Recognized: Yellow Card No. E223904

File No. E80271

Outline



Applications

Washing machine, inversion operation of capacitor motor, and other general controlling devices

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
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Repetitive peak off-state voltage ^{Note1}	V _{DRM}	800	V
Non-repetitive peak off-state voltage ^{Note1}	V _{DSM}	960	V

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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	8	A	Commercial frequency, sine full wave 360° conduction, Tc = 107°C
Surge on-state current	I _{TSM}	80	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	26	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V _{GM}	10	V	
Peak gate current	I _{GM}	2	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, T ₁ • T ₂ • G terminal to case

Notes: 1. Gate open.

Electrical Characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	—	_	2.0	mA	Tj = 150°C, V _{DRM} applied
On-state voltage		V _{TM}	—		1.6	V	$Tc = 25^{\circ}C$, $I_{TM} = 12 A$, Instantaneous measurement
Gate trigger voltage ^{Note2}	Ι	V_{FGTI}	—	_	1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V _{RGTI}	—	_	1.5	V	R _G = 330 Ω
	III	V _{RGTIII}	—	_	1.5	V	
Gate trigger current ^{Note2}	Ι	I _{FGTI}	—	_	30	mA	$Tj=25^{\circ}C,\ V_{D}=6\ V,\ R_{L}=6\ \Omega,$
	II	I _{RGTI}	—	_	30	mA	R _G = 330 Ω
	III	I _{RGTIII}	—	_	30	mA	
Gate non-trigger voltage		V _{GD}	0.2/0.1			V	Tj = 125°C/150°C,
							$V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	—	—	4.3	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-stat commutating voltage ^{Note4}	е	(dv/dt)c	10/1	_	—	V/µs	Tj = 125°C/150°C

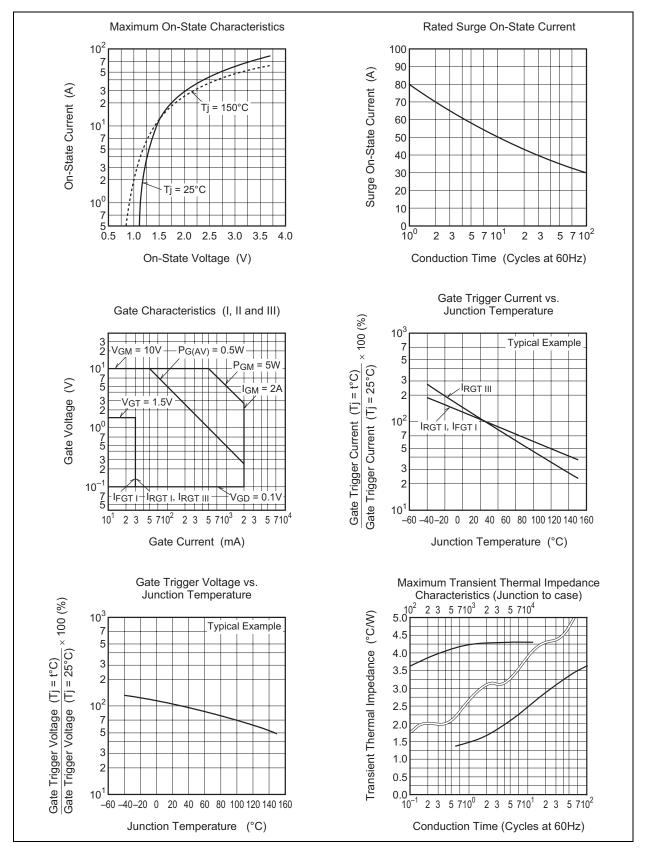
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance $R_{th\,(c\text{-}f)}$ in case of greasing is 0.5°C/W.

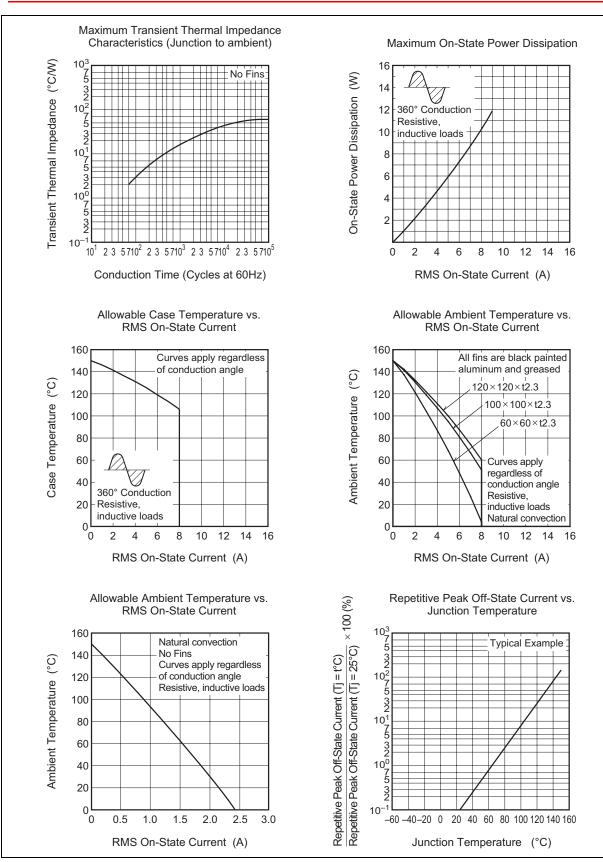
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C/150°C	Supply Voltage → Time		
2. Rate of decay of on-state commutating current (di/dt)c = - 4.0 A/ms	Main Current → Time		
3. Peak off-state voltage V _D = 400 V	Main Voltage → Time (dv/dt)c V _D		

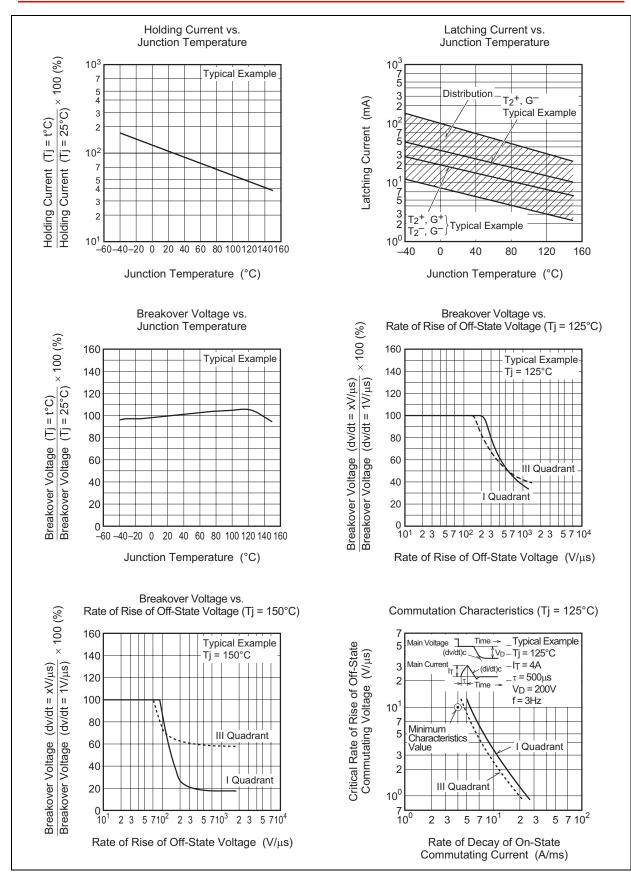
Performance Curves



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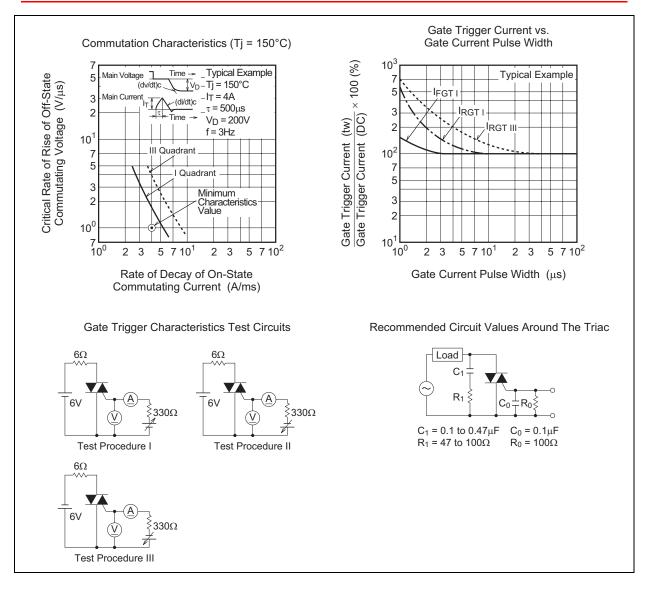


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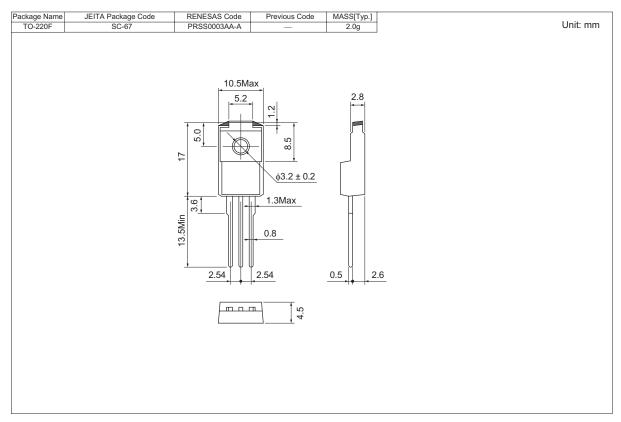


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Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR8PM-16LG
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR8PM-16LG-A8

Note : Please confirm the specification about the shipping in detail.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510